



DTA115T

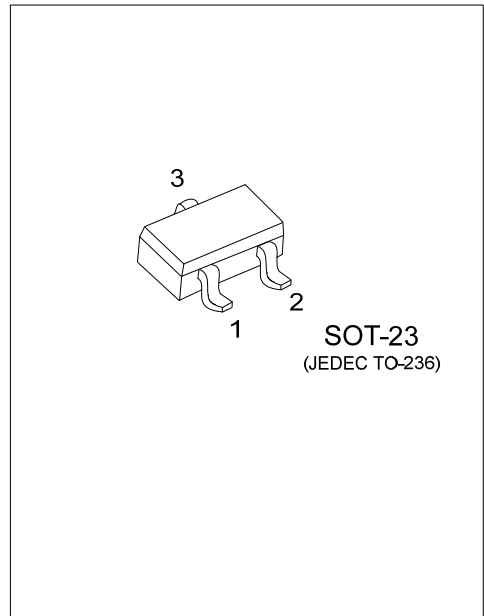
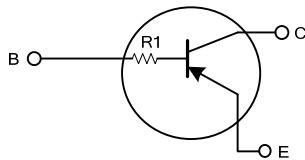
PNP SILICON TRANSISTOR

DIGITAL TRANSISTORS (BUILT-IN BIAS RESISTORS)

FEATURES

- * Built-in bias resistors that implies easy ON/OFF applications.
- * The bias resistors are thin-film resistors with complete isolation to allow positive input.

EQUIVALENT CIRCUIT



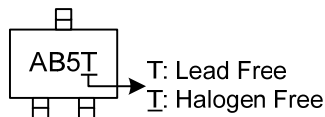
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
DTA115TL-AE3-R	DTA115TG-AE3-R	SOT-23	B	E	C	Tape Reel

Note: Pin Assignment: B: Base E: Emitter C: Collector

DTA115TG-AE3-R	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free, L: Lead Free
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MARKING



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■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL SPECIFICATIONS ($T_A=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-50\mu\text{A}$	-50			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-1\text{mA}$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-50\mu\text{A}$	-5			V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=-1\text{mA}$, $I_B=-0.1\text{mA}$			-0.3	V
Collector Cutoff Current	I_{CBO}	$V_{CB}=-50\text{V}$			-0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}$			-0.5	μA
DC Current Gain	h_{FE}	$V_{CE}=-5\text{V}$, $I_C=-1\text{mA}$	100	250	600	
Input Resistance	R_i		70	100	130	k Ω
Transition Frequency	f_T	$V_{CE}=-10\text{V}$, $I_E=5\text{mA}$, $f=100\text{MHz}$ (Note)		250		MHz

Note: Transition frequency of the device

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